

What is claimed is:

1. A phase shift mask comprising: a quartz substrate which includes an etch depth that corresponds to a 180 phase shift; and a pattern on the quartz substrate, wherein the pattern has a thickness which corresponds to at least one of a 0 and 360 degree phase shift.
2. A phase shift mask as recited in claim 1, wherein the pattern comprises attenuated film.
3. A phase shift mask as recited in claim 1, wherein the pattern comprises MoSi.
4. A method of manufacturing a phase shift mask, said method comprising: providing a quartz substrate having a pattern thereon having a thickness which corresponds to at least one of a 0 and 360 degree phase shift; and etching the quartz substrate to a depth that corresponds to a 180 phase shift.
5. A method as recited in claim 4, wherein the step of etching the quartz substrate comprises etching a pattern into the quartz substrate.
6. A method as recited in claim 4, wherein the step of etching the quartz substrate comprises etching where the pattern is not on the quartz substrate.
7. A method as recited in claim 4, wherein the step of providing a quartz substrate having a pattern thereon comprises coating a blank mask/resist onto a substrate of MoSi and quartz, writing and developing a pattern into the MoSi, and etching the MoSi.